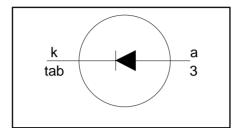
Rectifier diodes Schottky barrier

PBYR725D series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 20 \text{ V}/25 \text{ V}$$
 $I_{F(AV)} = 7.5 \text{ A}$
 $V_F \le 0.4 \text{ V}$

GENERAL DESCRIPTION

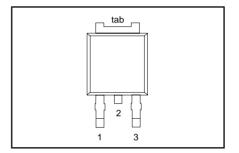
Schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR725D series is supplied in the SOT428 surface mounting package.

PINNING

PIN	DESCRIPTION	
1	no connection	
2	cathode ¹	
3	anode	
tab	cathode	

SOT428



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	ETER CONDITIONS		MAX.		UNIT
		PBYR7		20D	25D	
V_{RRM}	Peak repetitive reverse voltage		-	20	25	V
V_{RWM}	Working peak reverse voltage		-	20	25	V
V_R	Continuous reverse voltage	T _{mb} ≤ 119 °C	-	20	25	V
I _{F(AV)}	Average rectified forward current	square wave; $\delta = 0.5$; $T_{mb} \le 138$ °C	-	7.	.5	Α
I _{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{mb} \le 138$ °C	-	1	5	Α
I _{FSM}	Non-repetitive peak forward current	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM}(\text{max})}$	-		00 10	A A
I _{RRM}	Peak repetitive reverse surge current	pulse width and repetition rate limited by T _{i max}	-	,	1	Α
T _j	Operating junction temperature	,	-	15	50	°C
T _{stg}	Storage temperature		- 65	17	75	°C

¹ it is not possible to make connection to pin 2 of the SOT428 package

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction		-	-	3	K/W
R _{th i-a}	to mounting base Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	$I_{\rm F} = 7.5 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.33	0.4	٧
		$I_{\rm F} = 15 \text{A}; T_{\rm i} = 125 ^{\circ} \text{C}$	-	0.45	0.52	V
		$I_{\rm F} = 15 \text{A}$	-	0.52	0.62	V
I _R	Reverse current	$ \dot{V}_{R} = V_{RWM} $	-	0.2	5	mΑ
		$V_R = V_{RWM}$; $T_j = 100$ °C $V_R = 5$ V; $f = 1$ MHz, $T_i = 25$ °C to 125°C	-	15	30	mΑ
C_d	Junction capacitance	$V_R = 5 \text{ V}$; f = '1 MHz, $T_j = 25 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	580	-	pF

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PBYR725D series

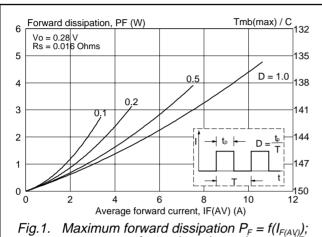


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

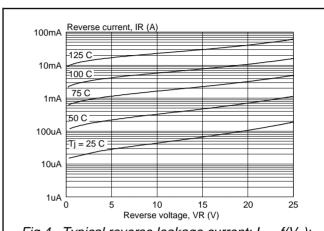


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter Ti

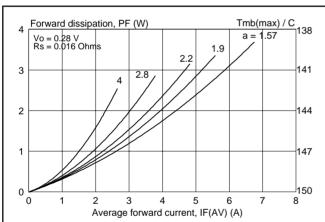
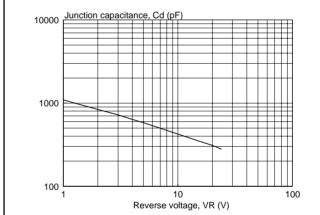
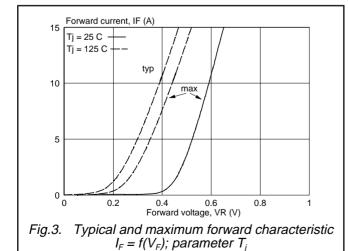
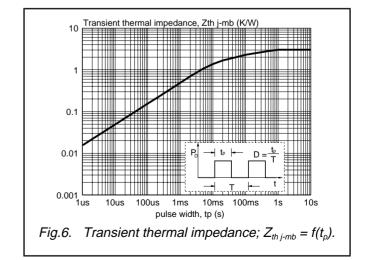


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = f(AV) $factor = I_{F(RMS)} / I_{F(AV)}$.



Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25^{\circ}\text{C}$ to 125°C . Fig.5.

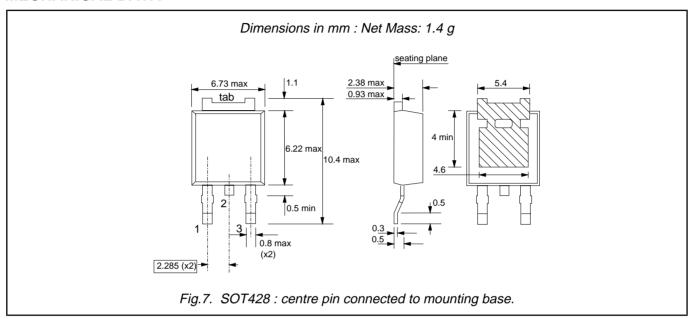




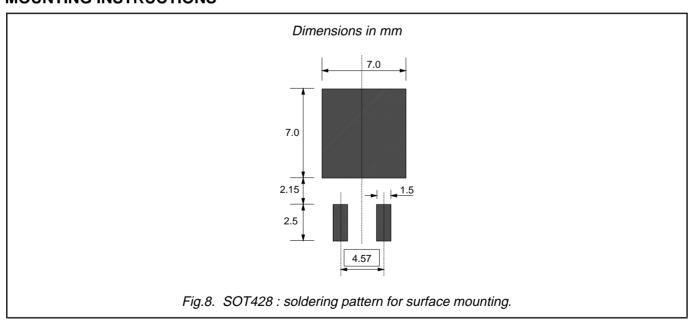
Philips Semiconductors Product specification

Rectifier diodes Schottky barrier PBYR725D series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

- 1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
- 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes	PBYR725D series
Schottky barrier	

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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